## **CPH3456**

## Power MOSFET 20V, 71mΩ, 3.5A, Single N-Channel



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#### **Features**

- ON-Resistance  $R_{DS}(on)1=54m\Omega$  (typ)
- 1.8V Drive
- Pb-Free, Halogen Free and RoHS Compliance

| VDSS | R <sub>DS</sub> (on) Max | ID Max |
|------|--------------------------|--------|
|      | 71 mΩ@4.5V               |        |
| 20V  | 103 mΩ@2.5V              | 3.5A   |
|      | 156 mΩ@1.8V              |        |

#### **Specifications**

#### **Absolute Maximum Ratings** at Ta = 25°C

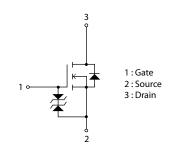
| Parameter  | Symbol           | Value       | Unit |
|--|------------------|-------------|------|
| Drain to Source Voltage  | V <sub>DSS</sub> | 20          | V    |
| Gate to Source Voltage   | VGSS             | ±12         | V    |
| Drain Current (DC)   | ID               | 3.5         | Α    |
| Drain Current (Pulse)<br>PW≤10μs, duty cycle≤1%                    | IDP              | 14          | А    |
| Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm) | PD               | 1.0         | W    |
| Junction Temperature   | Tj               | 150         | °C   |
| Storage Temperature  | Tstg             | –55 to +150 | °C   |

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

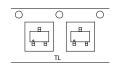
#### **Thermal Resistance Ratings**

| Parameter  | Symbol           | Value | Unit |
|--|------------------|-------|------|
| Junction to Ambient When mounted on ceramic substrate (900mm²×0.8mm) | R <sub>θJA</sub> | 125   | °C/W |

## Electrical Connection N-Channel



Packing Type:TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

<sup>\*</sup> Machine Model

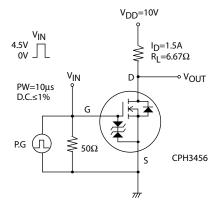
#### **CPH3456**

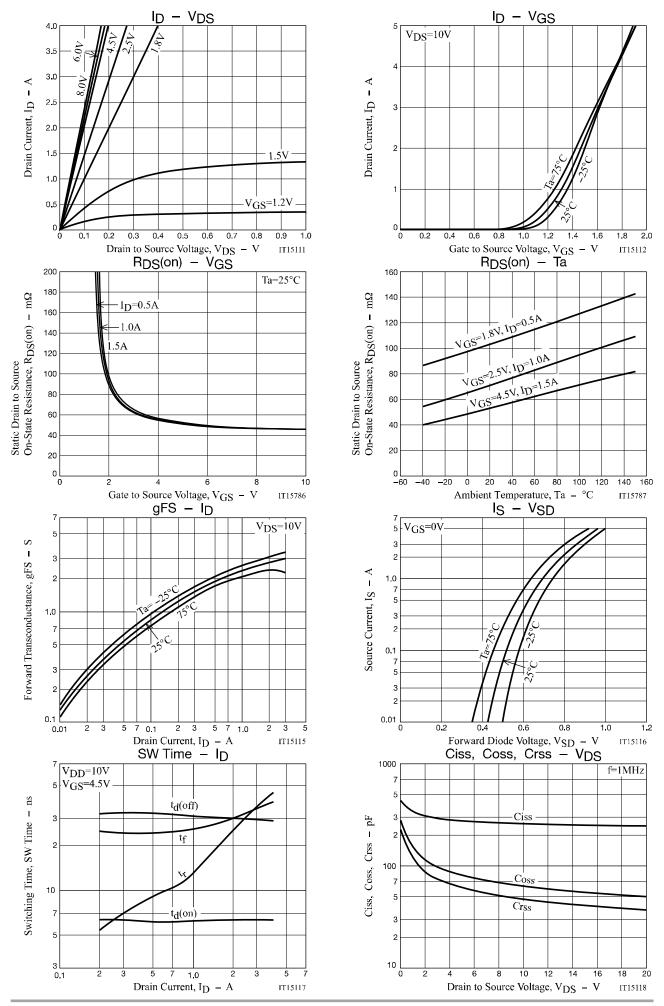
#### **Electrical Characteristics** at $Ta = 25^{\circ}C$

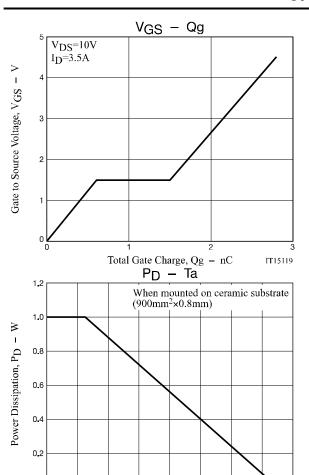
| Parameter                                  | Symbol Conditions     | 0485  |     | Value |      |    |
|--|-----------------------|---|-----|-------|------|----|
| Parameter                                  |                       | min   | typ | max   | Unit |    |
| Drain to Source Breakdown Voltage          | V(BR)DSS              | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V                          | 20  |       |      | ٧  |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V                         |     |       | 1    | μΑ |
| Gate to Source Leakage Current             | IGSS                  | V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V                         |     |       | ±10  | μΑ |
| Gate Threshold Voltage                     | V <sub>GS</sub> (th)  | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA                         | 0.4 |       | 1.3  | >  |
| Forward Transconductance                   | gFS .                 | V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A                        |     | 2.8   |      | S  |
| Static Drain to Source On-State Resistance | R <sub>DS</sub> (on)1 | I <sub>D</sub> =1.5A, V <sub>GS</sub> =4.5V                       |     | 54    | 71   | mΩ |
|  | R <sub>DS</sub> (on)2 | I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V                         |     | 73    | 103  | mΩ |
|  | R <sub>DS</sub> (on)3 | I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V                       |     | 104   | 156  | mΩ |
| Input Capacitance                          | Ciss                  | V <sub>DS</sub> =10V, f=1MHz                                      |     | 260   |      | pF |
| Output Capacitance                         | Coss                  |   |     | 65    |      | pF |
| Reverse Transfer Capacitance               | Crss                  |   |     | 50    |      | pF |
| Turn-ON Delay Time                         | t <sub>d</sub> (on)   |   |     | 6.2   |      | ns |
| Rise Time                                  | t <sub>r</sub>        | See specified Test Circuit  |     | 19    |      | ns |
| Turn-OFF Delay Time                        | t <sub>d</sub> (off)  |   |     | 30    |      | ns |
| Fall Time                                  | tf                    |   |     | 28    |      | ns |
| Total Gate Charge                          | Qg                    | V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A |     | 2.8   |      | nC |
| Gate to Source Charge                      | Qgs                   |   |     | 0.6   |      | nC |
| Gate to Drain "Miller" Charge              | Qgd                   | ]   |     | 0.9   |      | nC |
| Forward Diode Voltage                      | V <sub>SD</sub>       | I <sub>S</sub> =3.5A, V <sub>GS</sub> =0V                         |     | 0.85  | 1.2  | ٧  |

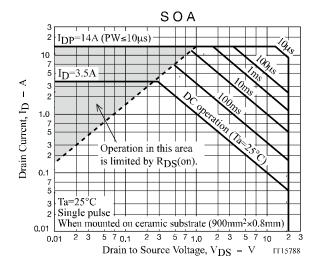
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

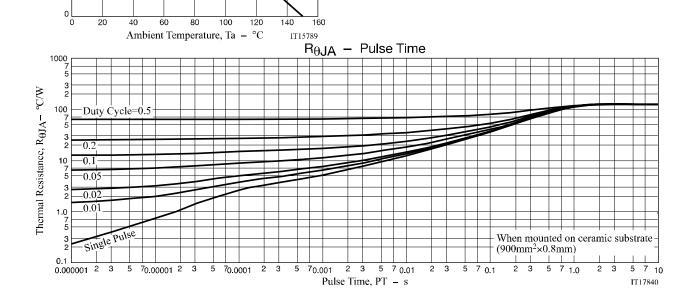
### **Switching Time Test Circuit**











#### **Package Dimensions**

CPH3456-TL-H/ CPH3456-TL-W

#### CPH3

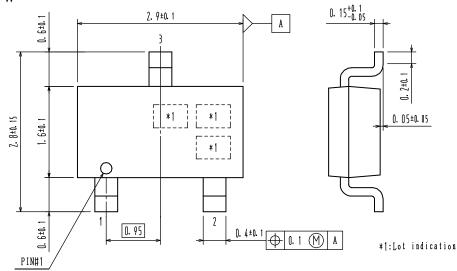
CASE 318BA ISSUE O

Unit: mm

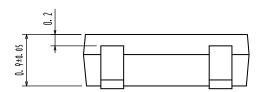
1: Gate

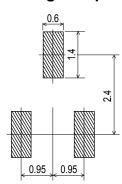
2 : Source

3: Drain



# Recommended Soldering Footprint





#### ORDERING INFORMATION

| Device       | Package        | Shipping    | Note           |  |
|--------------|----------------|-------------|----------------|--|
| CPH3456-TL-H | CPH3, SC-59    | 3,000       | Pb-Free<br>and |  |
| CPH3456-TL-W | SOT-23, TO-236 | pcs. / reel | Halogen Free   |  |

Note on usage: Since the CPH3456 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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